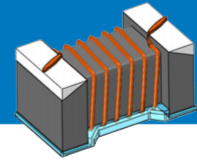


# Wire Wound Chip Ferrite Inductor – MWSD – FE Series



Operating temp. : -40°C ~+85°C

## FEATURES

- ◆ Small chip suitable for surface mounting
- ◆ Large inductance with ferrite material
- ◆ Single-sided package, thinner than WL-FS Series

## APPLICATIONS

- ◆ Mobile phones and other electronic devices
- ◆ Bluetooth modules and TWS earphones

## PRODUCT IDENTIFICATION

1 <b>MWSD</b>	2 <b>1608</b>	3 <b>F</b>	4 <b>E</b>	5 <b>2R2</b>	6 <input type="checkbox"/>	7 <b>T</b>
------------------	------------------	---------------	---------------	-----------------	-------------------------------	---------------

1	Type
MWSD	Wire Wound Chip Inductor

2	External Dimensions (L×W) (mm)	
1608 [0603]	1.6×0.8	
2012 [0805]	2.0×1.25	

3	Material Code	
F	Ferrite	

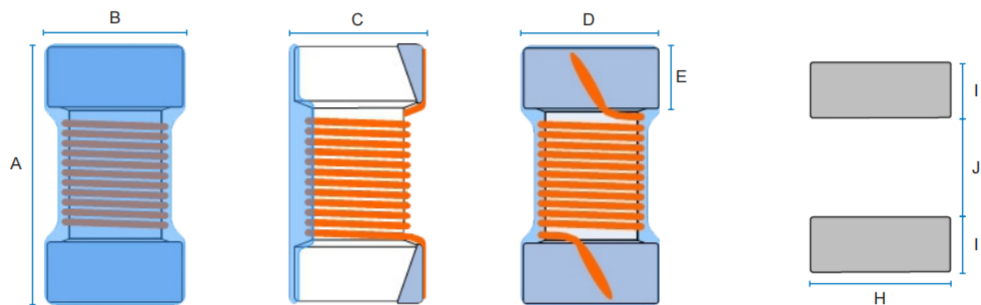
4	Internal Code	
E	Internal Code	

5	Nominal Inductance	
Example	Nominal Value	
2R2	2.2μH	
100	10μH	

6	Inductance Tolerance	
K	±10%	
M	±20%	

8	Packing	
B	Bulk Package	
T	Tape & Reel	

## SHAPE AND DIMENSIONS



Series	A	B	C	D Typ.	E Ref.	H Ref.	I Ref.	J Ref.
MWSD1608FE	1.80Max.	1.20Max.	1.00Max.	0.92	0.30	1.15	0.64	0.64
MWSD2012FE	2.40Max.	1.65Max.	1.30Max.	1.28	0.48	1.50	1.02	0.96

Unit: mm

**SPECIFICATIONS** MWSD1608FE TYPE

Part Number	Inductance	Tolerance	L Test Freq.	Typ. Self-resonant Frequency	DC Resistance	Typ. Rated Current
Units	μH	-	MHz	MHz	Ω	mA
Symbol	L	-	Freq.	S.R.F	DCR	I <sub>r</sub>
MWSD1608FE1R0 □ T	1.0	K,M	7.9	340	0.30±30%	700
MWSD1608FE1R8 □ T	1.8	K,M	7.9	150	0.50±30%	500
MWSD1608FE2R2 □ T	2.2	K,M	7.9	103	0.56±30%	580
MWSD1608FE3R3 □ T	3.3	K,M	7.9	65	0.68±30%	450
MWSD1608FE4R7 □ T	4.7	K,M	7.9	51	0.97±30%	420
MWSD1608FE6R8 □ T	6.8	K,M	7.9	43	1.50±30%	340
MWSD1608FE100 □ T	10	K,M	2.5	36	1.85±30%	280
MWSD1608FE150 □ T	15	K,M	2.5	29	2.60±30%	240
MWSD1608FE220 □ T	22	K,M	2.5	24	2.80±30%	200
MWSD1608FE470 □ T	47	K,M	2.5	14	6.65±30%	100

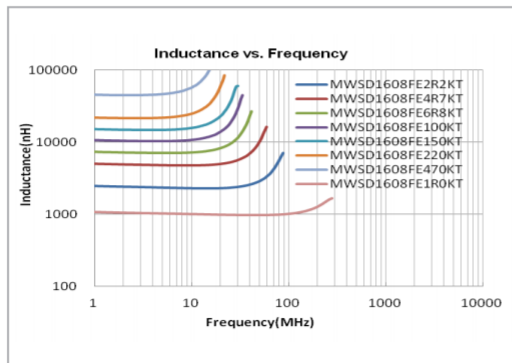
MWSD2012FE TYPE

Part Number	Inductance	Tolerance	L Test Freq.	Typ. Self-resonant Frequency	DC Resistance	Typ. Rated Current
Units	μH	-	MHz	MHz	Ω	mA
Symbol	L	-	Freq.	S.R.F	DCR	I <sub>r</sub>
MWSD2012FER68 □ T	0.68	K,M	7.9	100	0.24±30%	660
MWSD2012FE2R2 □ T	2.2	K,M	7.9	87	0.22±30%	1040
MWSD2012FE3R3 □ T	3.3	K,M	7.9	70	0.28±30%	1000
MWSD2012FE4R7 □ T	4.7	K,M	7.9	51	0.43±30%	840
MWSD2012FE6R8 □ T	6.8	K,M	7.9	46	0.68±30%	700
MWSD2012FE100 □ T	10	K,M	2.5	31	0.85±30%	560
MWSD2012FE150 □ T	15	K,M	2.5	28	1.40±30%	380
MWSD2012FE180 □ T	180	K,M	2.5	27	1.73±30%	200
MWSD2012FE220 □ T	22	K,M	2.5	20	1.76±30%	340
MWSD2012FE330 □ T	33	K,M	2.5	8	2.00±30%	220
MWSD2012FE470 □ T	47	K,M	1.0	15	3.40±30%	280
MWSD2012FE101 □ T	100	K,M	1.0	9	7.50±30%	180
MWSD2012FE111 □ T	110	K,M	1.0	9	7.50±30%	100

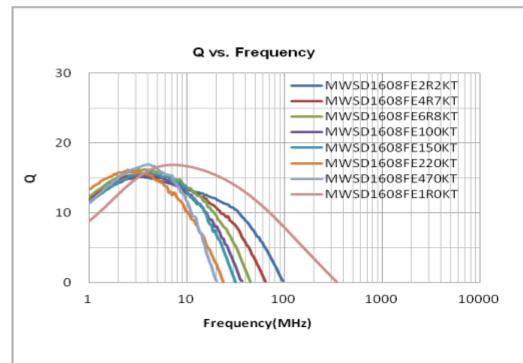
**TYPICAL ELECTRICAL CHARACTERISTICS**

MWSD1608FE TYPE

Inductance vs. Frequency Characteristics



Q vs. Frequency Characteristics

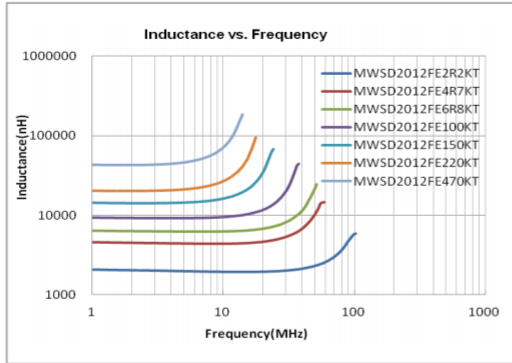


Multilayer Chip Ferrite Inductor  
Multilayer Chip Inductor for Choke  
Multilayer Chip Power Inductor  
Multilayer Ultra High Q Chip Ceramic Inductor  
Multilayer High Q Chip Ceramic Inductor  
Multilayer Chip Ceramic Inductor  
Multilayer High Frequency Chip Ceramic Inductor  
Wire Wound Chip Ceramic Inductor  
Wire Wound Chip Ferrite Inductor  
SMD Power Inductor

TYPICAL  
ELECTRICAL  
CHARACTERISTICS

MWSD2012FE TYPE

Inductance vs. Frequency Characteristics



Q vs. Frequency Characteristics

